

3A Dual High-Speed Power MOSFET Drivers

Features

- · High Peak Output Current: 3A
- Wide Input Supply Voltage Operating Range:
 4.5V to 18V
- High Capacitive Load Drive Capability: 1800 pF in 25 nsec
- Short Delay Times: <40 nsec (typ)
- · Matched Rise/Fall Times
- · Low Supply Current:
 - With Logic '1' Input 3.5 mA (Max)
- With Logic '0' Input 350 µA (Max)
- Low Output Impedance: 3.5Ω (typ)
- Latch-Up Protected: Will Withstand 1.5A Reverse Current
- Logic Input Will Withstand Negative Swing Up To 5V
- ESD Protected: 4 kV
- Pin compatible with the TC1426/TC1427/TC1428, TC4426/TC4427/TC4428 and TC4426A/ TC4427A/TC4428A devices.

Applications

- · Switch Mode Power Supplies
- Pulse Transformer Drive
- Line Drivers

General Description

The TC4423/TC4424/TC4425 devices are a family of 3A, dual output buffers/MOSFET drivers. Pin compatible with both the TC4426/4427/4428 and TC426/427/428 families (dual 1.5A drivers), the TC4423/TC4424/TC4425 family has an increased latch-up current rating of 1.5A, making them even more robust for operation in harsh electrical environments.

As MOSFET drivers, the TC4423/TC4424/TC4425 can easily charge 1800 pF gate capacitance in under 35 nsec and provide low enough impedances in both the ON and OFF states to ensure the MOSFET's intended state will not be affected, even by large transients.

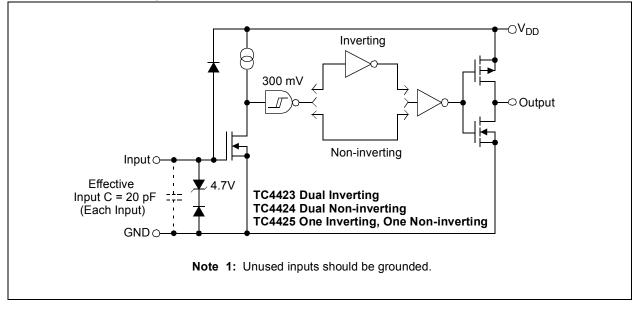
The TC4423/TC4424/TC4425 inputs may be driven directly from either TTL or CMOS (2.4V to 18V). In addition, 300 mV of hysteresis is built-in to provide noise immunity and to allow the device to be driven from slowly rising or falling waveforms.

Package Types

= 1(:4425	TC4423 NC OUT A VDD OUT B	TC4424 NC OUT A V _{DD} OUT B	TC4425 NC OUT A V _{DD} OUT B					
16-Pin SOIC (Wide) NC 1 IN A 2 NC 3 GND 4 GND 5 NC 6 IN B 7 NC 8	TC442: ↓ 16 NC 15 OUT 14 OUT 13 V _{DD} 11 OUT 11 OUT 10 OUT 9 NC	NC A OUT A OUT V _{DD} B OUT	A OUT A V _{DD} V _{DD} B OUT B					
NC = No Connection NOTE: Duplicate pins must be connected for proper operation.								

TC4423/TC4424/TC4425

Functional Block Diagram



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings*

Supply Vo	Itage					+22V
Input Volta	age, IN A d	or IN B				
	-		(\	/ _{DD} + 0	.3V) to	(GND – 5V)
Package F	ower Dis	sipation	$(T_A \le 7$	0°C)		
PDIP						730 mW
CER	DIP					800 mW
SOIC	;					470 mW
*Notice	Stresses	above	those	listed	under	"Maximum

*Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS

Electrical Specifications: Unless otherwise indicated, $T_A = +25^{\circ}C$, with $4.5V \le V_{DD} \le 18V$.								
Parameters	Sym	Min	Тур	Мах	Units	Conditions		
Input								
Logic '1', High Input Voltage	V _{IH}	2.4	—		V			
Logic '0', Low Input Voltage	V _{IL}	_	—	0.8	V			
Input Current	I _{IN}	-1	—	1	μA	$0V \le V_{IN} \le V_{DD}$		
Output								
High Output Voltage	V _{OH}	V _{DD} – 0.025	_	—	V			
Low Output Voltage	V _{OL}		—	0.025	V			
Output Resistance, High	R _{OH}	_	2.8	5	Ω	I _{OUT} = 10 mA, V _{DD} = 18V		
Output Resistance, Low	R _{OL}	_	3.5	5	Ω	I _{OUT} = 10 mA, V _{DD} = 18V		
Peak Output Current	I _{PK}	_	3		Α			
Latch-Up Protection Withstand Reverse Current	I _{REV}		>1.5	—	A	Duty cycle \leq 2%, t \leq 300 µsec.		
Switching Time (Note 1)					1	•		
Rise Time	t _R		23	35	nsec	Figure 4-1 , Figure 4-2 , C _L = 1800 pF		
Fall Time	t _F		25	35	nsec	Figure 4-1 , Figure 4-2 , C _L = 1800 pF		
Delay Time	t _{D1}		33	75	nsec	Figure 4-1 , Figure 4-2 , C _L = 1800 pF		
Delay Time	t _{D2}		38	75	nsec	Figure 4-1 , Figure 4-2 , C _L = 1800 pF		
Power Supply			•			•		
Power Supply Current	۱ _S		1.5 0.15	2.5 0.25	mA	V _{IN} = 3V (Both inputs) V _{IN} = 0V (Both inputs)		

Note 1: Switching times ensured by design.

DC CHARACTERISTICS (OVER OPERATING TEMPERATURE RANGE)

Electrical Specifications: Unless otherwise indicated, operating temperature range with 4.5V \leq V _{DD} \leq 18V.										
Parameters	Sym	Min	Тур	Мах	Units	Conditions				
Input										
Logic '1', High Input Voltage	V _{IH}	2.4	_		V					
Logic '0', Low Input Voltage	V_{IL}	—	—	0.8	V					
Input Current	I _{IN}	-10	—	+10	μA	$0V \le V_{IN} \le V_{DD}$				
Output										
High Output Voltage	V _{OH}	V _{DD} – 0.025	_	—	V					
Low Output Voltage	V _{OL}	—	—	0.025	V					
Output Resistance, High	R _{OH}	—	3.7	8	Ω	I _{OUT} = 10 mA, V _{DD} = 18V				
Output Resistance, Low	R _{OL}	—	4.3	8	Ω	I _{OUT} = 10 mA, V _{DD} = 18V				
Peak Output Current	I _{PK}	—	3.0	—	А					
Latch-Up Protection Withstand Reverse Current	I _{REV}	—	>1.5	—	A	Duty cycle \leq 2%, t \leq 300 µsec				
Switching Time (Note 1)					•	•				
Rise Time	t _R	—	28	60	nsec	Figure 4-1 , Figure 4-2 , C _L = 1800 pF				
Fall Time	t _F	—	32	60	nsec	Figure 4-1 , Figure 4-2 , C _L = 1800 pF				
Delay Time	t _{D1}	—	32	100	nsec	Figure 4-1 , Figure 4-2 , C _L = 1800 pF				
Delay Time	t _{D2}	—	38	100	nsec	Figure 4-1 , Figure 4-2 , C _L = 1800 pF				
Power Supply		·			•	·				
Power Supply Current	۱ _S	—	2.0 0.2	3.5 0.3	mA	V _{IN} = 3V (Both inputs) V _{IN} = 0V (Both inputs)				

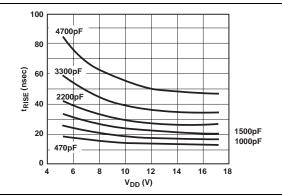
Note 1: Switching times ensured by design.

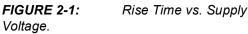
TEMPERATURE CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, all parameters apply with $4.5V \le V_{DD} \le 18V$.									
Parameters	Sym	Min	Тур	Max	Units	Conditions			
Temperature Ranges									
Specified Temperature Range (C)	T _A	0	_	+70	°C				
Specified Temperature Range (E)	T _A	-40	_	+85	°C				
Specified Temperature Range (M)	T _A	-55	_	+125	°C				
Specified Temperature Range (V)	T _A	-40	_	+125	°C				
Maximum Junction Temperature	TJ	—	—	+150	°C				
Storage Temperature Range	T _A	-65	—	+150	°C				
Package Thermal Resistances									
Thermal Resistance, 8L-PDIP	θ_{JA}	_	125	_	°C/W				
Thermal Resistance, 8L-CERDIP	θ_{JA}	_	150	_	°C/W				
Thermal Resistance, 16L-SOIC	θ_{JA}	_	155	_	°C/W				

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.





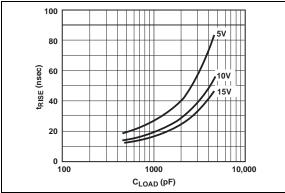


FIGURE 2-2: Rise Time vs. Capacitive Load.

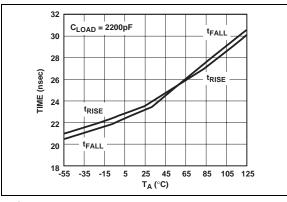


FIGURE 2-3: Temperature.

Rise and Fall Times vs.

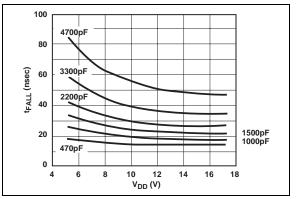


FIGURE 2-4:Fall Time vs. SupplyVoltage.

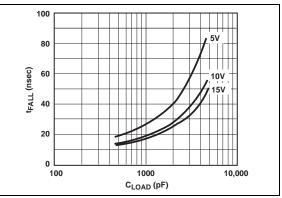


FIGURE 2-5: Fall Time vs. Capacitive Load.

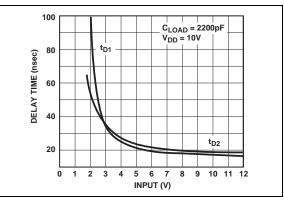


FIGURE 2-6: Amplitude.

Propagation Delay vs. Input

Typical Performance Curves (Continued)

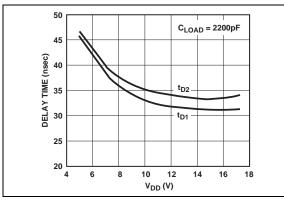


FIGURE 2-7: Propagation Delay Time vs. Supply Voltage.

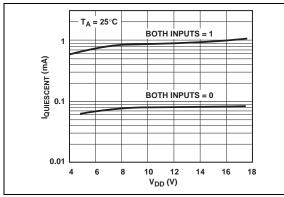


FIGURE 2-8: Quiescent Current vs. Supply Voltage.

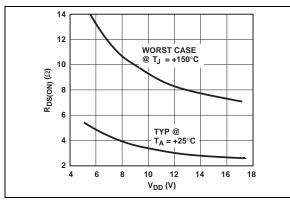


FIGURE 2-9:Output Resistance (OutputHigh) vs. Supply Voltage.

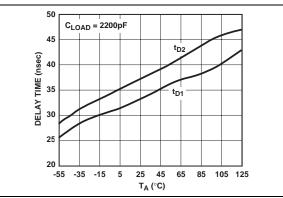


FIGURE 2-10: Propagation Delay Time vs. Temperature.

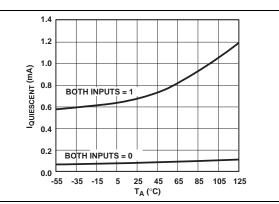


FIGURE 2-11: Quiescent Current vs. Temperature.

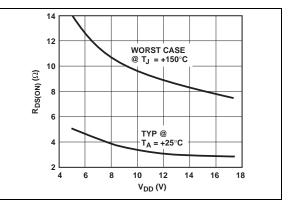
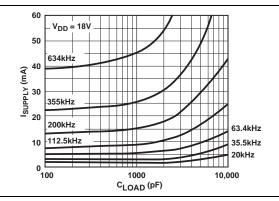
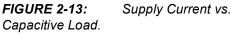


FIGURE 2-12: Output Resistance (Output Low) vs. Supply Voltage.

Typical Performance Curves (Continued)

Note: Load on single output only





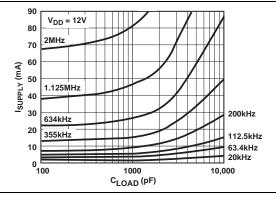


FIGURE 2-14: Supply Current vs. Capacitive Load.

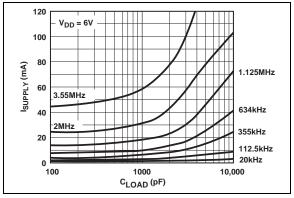


FIGURE 2-15: Supply Current vs. Capacitive Load.

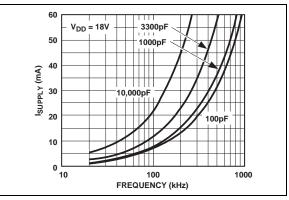


FIGURE 2-16: Supply Current vs. Frequency.

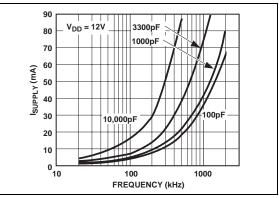


FIGURE 2-17: Supply Current vs. Frequency.

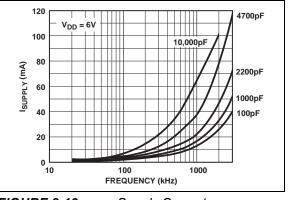


FIGURE 2-18: Frequency.

Supply Current vs.

Typical Performance Curves (Continued)

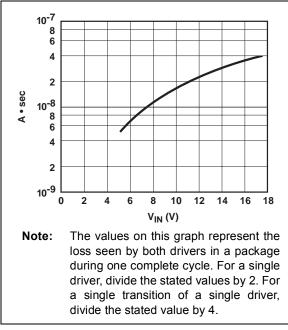


FIGURE 2-19: TC4423 Crossover Energy.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TADLE 3-1						
8-Pin PDIP, CERDIP	16-Pin SOIC (Wide)	Symbol	Description			
1	1	NC	No connect			
2	2	IN A	Input A			
—	3	NC	No connect			
3	4	GND	Ground			
—	5	GND	Ground			
—	6	NC	No connect			
4	7	IN B	Input B			
_	8	NC	No connect			
—	9	NC	No connect			
5	10	OUT B	Output B			
_	11	OUT B	Output B			
6	12	V _{DD}	Supply input			
_	13	V _{DD}	Supply input			
7	14	OUT A	Output A			
—	15	OUT A	Output A			
8	16	NC	No connect			

TABLE 3-1:	PIN FUNCTION TABLE
IADLE J-I.	

Note 1: Duplicate pins must be connected for proper operation.

3.1 Input A

Input A is a TTL/CMOS-compatible input that controls Output A. This input has 300 mV of hysteresis between the high and low input levels that allows it to be driven from slow rising and falling signals and provide noise immunity.

3.2 Input B

Input B is a TTL/CMOS-compatible input that controls Output B. This input has 300 mV of hysteresis between the high and low input levels that allows it to be driven from slow rising and falling signals and provide noise immunity.

3.3 Output B

Output B is a CMOS push-pull output that is capable of sourcing and sinking 3A peaks of current (V_{DD} = 18V). The low output impedance ensures the gate of the external MOSFET will stay in the intended state even during large transients. This output also has a reverse current latch-up rating of 1.5A.

3.4 Output A

Output A is a CMOS push-pull output that is capable of sourcing and sinking 3A peaks of current (V_{DD} = 18V). The low output impedance ensures the gate of the external MOSFET will stay in the intended state even during large transients. This output also has a reverse current latch-up rating of 1.5A.

3.5 Supply Input (V_{DD})

 V_{DD} is the bias supply input for the MOSFET driver and has a voltage range of 4.5V to 18V. This input must be decoupled to ground with a local ceramic capacitor. This bypass capacitor provides a localized lowimpedance path for the peak currents that are to be provided to the load.

3.6 Ground (GND)

Ground is the device return pin. The ground pin(s) should have a low-impedance connection to the bias supply source return. High peak currents will flow out the ground pin(s) when the capacitive load is being discharged.

4.0 APPLICATIONS INFORMATION

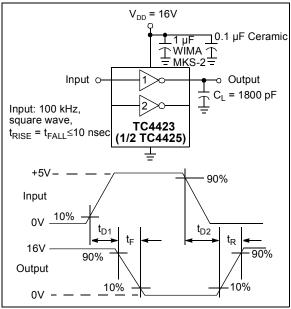


FIGURE 4-1: Inverting Driver Switching Time.

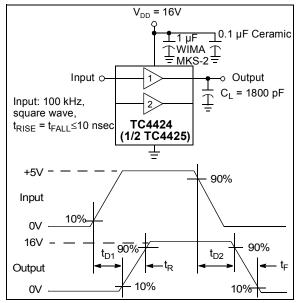
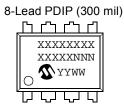


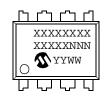
FIGURE 4-2: Non-inverting Driver Switching Time.

5.0 PACKAGING INFORMATION

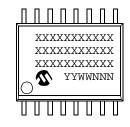
5.1 Package Marking Information

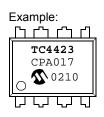


8-Lead CERDIP (300 mil)



16-Lead SOIC (300 mil)





Example:



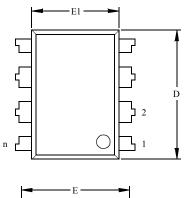
Example:

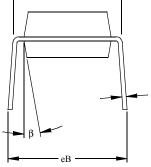


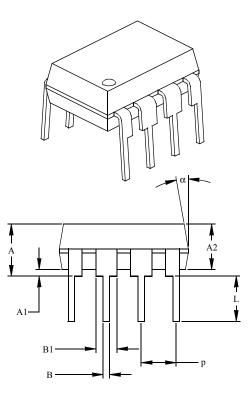
Legend	I: XXX YY WW NNN	Customer specific information* Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code
Note:	be carried	nt the full Microchip part number cannot be marked on one line, it will over to the next line thus limiting the number of available characters er specific information.

* Standard marking consists of Microchip part number, year code, week code, traceability code (facility code, mask rev#, and assembly code). For marking beyond this, certain price adders apply. Please check with your Microchip Sales Office.

8-Lead Plastic Dual In-line (P) – 300 mil (PDIP)







	Units		INCHES*		Ν	IILLIMETERS	3
Dimensior	n Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.100			2.54	
Top to Seating Plane	Α	.140	.155	.170	3.56	3.94	4.32
Molded Package Thickness	A2	.115	.130	.145	2.92	3.30	3.68
Base to Seating Plane	A1	.015			0.38		
Shoulder to Shoulder Width	Е	.300	.313	.325	7.62	7.94	8.26
Molded Package Width	E1	.240	.250	.260	6.10	6.35	6.60
Overall Length	D	.360	.373	.385	9.14	9.46	9.78
Tip to Seating Plane	L	.125	.130	.135	3.18	3.30	3.43
Lead Thickness	с	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.045	.058	.070	1.14	1.46	1.78
Lower Lead Width	В	.014	.018	.022	0.36	0.46	0.56
Overall Row Spacing §	eB	.310	.370	.430	7.87	9.40	10.92
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15

* Controlling Parameter § Significant Characteristic

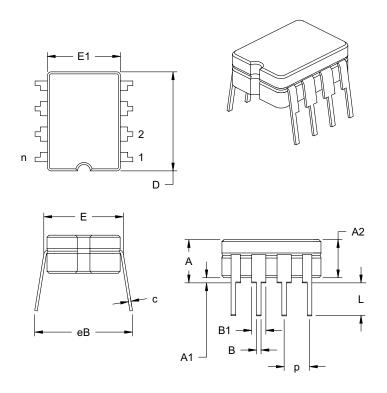
Notes:

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side. JEDEC Equivalent: MS-001

Drawing No. C04-018

DS21421C-page 12

8-Lead Ceramic Dual In-line – 300 mil (CERDIP)



	Units		INCHES*		N	IILLIMETERS	5
Dimensio	n Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.100			2.54	
Top to Seating Plane	A	.160	.180	.200	4.06	4.57	5.08
Standoff §	A1	.020	.030	.040	0.51	0.77	1.02
Shoulder to Shoulder Width	E	.290	.305	.320	7.37	7.75	8.13
Ceramic Pkg. Width	E1	.230	.265	.300	5.84	6.73	7.62
Overall Length	D	.370	.385	.400	9.40	9.78	10.16
Tip to Seating Plane	L	.125	.163	.200	3.18	4.13	5.08
Lead Thickness	С	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.045	.055	.065	1.14	1.40	1.65
Lower Lead Width	В	.016	.018	.020	0.41	0.46	0.51
Overall Row Spacing	eB	.320	.360	.400	8.13	9.15	10.16
Controlling Poromotor	•	•					

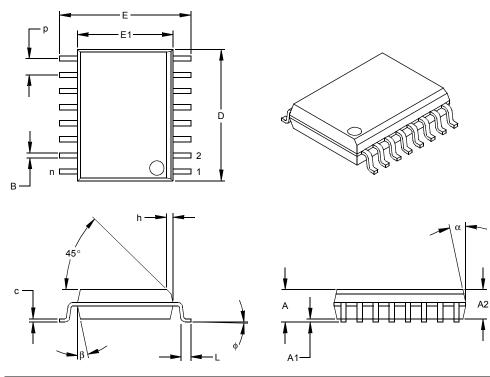
*Controlling Parameter

JEDEC Equivalent: MS-030

Drawing No. C04-010

TC4423/TC4424/TC4425

16-Lead Plastic Small Outline (SO) – Wide, 300 mil (SOIC)



	Units		INCHES*		N	IILLIMETERS	5
Dimensio	n Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		16			16	
Pitch	р		.050			1.27	
Overall Height	Α	.093	.099	.104	2.36	2.50	2.64
Molded Package Thickness	A2	.088	.091	.094	2.24	2.31	2.39
Standoff §	A1	.004	.008	.012	0.10	0.20	0.30
Overall Width	Е	.394	.407	.420	10.01	10.34	10.67
Molded Package Width	E1	.291	.295	.299	7.39	7.49	7.59
Overall Length	D	.398	.406	.413	10.10	10.30	10.49
Chamfer Distance	h	.010	.020	.029	0.25	0.50	0.74
Foot Length	L	.016	.033	.050	0.41	0.84	1.27
Foot Angle	φ	0	4	8	0	4	8
Lead Thickness	С	.009	.011	.013	0.23	0.28	0.33
Lead Width	В	.014	.017	.020	0.36	0.42	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

* Controlling Parameter

§ Significant Characteristic

Notes:

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

JEDEC Equivalent: MS-013

Drawing No. C04-102

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	X	/ <u>XX</u>	Ex	amples:	
Device	Femperature	Package	a)	TC4423COE:	Commerical Temperature, SOIC package.
	Range	1	b)	TC4423CPA:	Commercial Temperature, PDIP package.
T	TC4424: 3A	A Dual MOSFET Driver, Inverting A Dual MOSFET Driver, Non-Inverting	c)	TC4423MJA:	Military Temperature, Ceramic DIP package.
	TC4425: 3A	A Dual MOSFET Driver, Complementary	a)	TC4424COE713:	Commerical Temperature,
Temperature Range:	E = -40	C to +70°C)°C to +85°C 5°C to +125°C (CERDIP only)			SOIC package, Tape and Reel.
		°C to +125°C	b)	TC4424EPA:	Commercial Temperature, PDIP package.
Package:	JA = Cer OE = SO	astic DIP, (300 mil body), 8-lead eramic DIP, (300 mil body), 8-lead DIC (Wide), 16-pin	a)	TC4425EOE:	Extended Temperature, SOIC package.
	0E713 = SO	DIC (Wide), 16-pin (Tape and Reel)	b)	TC4425CPA:	Commercial Temperature, PDIP package.

Sales and Support

Data Sheets

Products supported by a preliminary Data Sheet may have an errata sheet describing minor operational differences and recommended workarounds. To determine if an errata sheet exists for a particular device, please contact one of the following:

1. Your local Microchip sales office

- 2. The Microchip Corporate Literature Center U.S. FAX: (480) 792-7277
- 3. The Microchip Worldwide Site (www.microchip.com)

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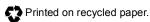
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